

	Type	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	0	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and "ohmic layer" and "reflector layer"	USPAT	2001/03/15 09:34	
2	BRS	0	"light emitting device" and semiconductor and "p-type layer" and "n-type layer" and "ohmic layer" and "reflector layer"	USPAT	2001/03/12 09:51	
3	BRS	0	"light emitting device" and semiconductor and "p-type layer" and "ohmic layer" and "reflector layer"	USPAT	2001/03/12 09:51	
4	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "reflector layer"	USPAT	2001/03/12 09:52	
5	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and "n-type layer"	USPAT	2001/03/12 09:53	
6	BRS	1	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer"	USPAT	2001/03/12 10:28	
7	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and "reflector layer"	USPAT	2001/03/12 10:23	
8	BRS	13	"light emitting device" and semiconductor and "ohmic layer"	USPAT	2001/03/12 10:07	
9	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and "mirror layer"	USPAT	2001/03/12 10:23	
10	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and "reproducer layer"	USPAT	2001/03/12 10:23	

	Type	Hits	Search Text	DBs	Time Stamp	Comments
11	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and "replicator layer"	USPAT	2001/03/12 10:24	
12	BRS	0	"light emitting diode" and semiconductor and "ohmic layer" and "p-type layer" and "replicator layer"	USPAT	2001/03/12 10:24	
13	BRS	0	"light emitting diode" and semiconductor and "ohmic layer" and "p-type layer" and "replicate layer"	USPAT	2001/03/12 10:24	
14	BRS	0	"light emitting diode" and semiconductor and "ohmic layer" and "p-type layer" and "replicate layer"	USPAT	2001/03/12 10:25	
15	BRS	0	"light emitting diode" and semiconductor and "ohmic layer" and "p-type layer" and "replicate"	USPAT	2001/03/12 10:25	
16	BRS	0	"light emitting diode" and semiconductor and "ohmic layer" and "p-type layer" and "mirror"	USPAT	2001/03/12 10:26	
17	BRS	0	"light emitting diode" and semiconductor and "ohmic layer" and "p-type layer" and "reproduce"	USPAT	2001/03/12 10:26	
18	BRS	0	"light emitting diode" and semiconductor layer and "ohmic layer" and "p-type layer"	USPAT	2001/03/12 10:27	
19	BRS	0	"light emitting diode" and "ohmic layer" and "p-type layer"	USPAT	2001/03/12 10:27	
20	BRS	0	"light emitting diode" and semiconductor and "ohmic layer" and "p-type layer"	USPAT	2001/03/12 10:27	
21	BRS	1	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer"	USPAT	2001/03/12 10:29	
22	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and replicator	USPAT	2001/03/12 10:29	

	Type	Hits	Search Text	DBs	Time Stamp	Comments
23	BRS	1	"light emitting device" and semiconductor and "ohmic layer" and p-type adj layer	USPAT	2001/03/12 10:29	
24	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and p-type adj layer and replicator	USPAT	2001/03/12 10:30	
25	BRS	0	"light emitting device" and semiconductor adj layer and "ohmic layer" and p-type adj layer	USPAT	2001/03/12 10:30	
26	BRS	1	"light emitting device" and semiconductor adj layers and "ohmic layer" and p-type adj layer	USPAT	2001/03/12 10:32	
27	BRS	1	"light emitting device" and semiconductor adj layers and "ohmic layer" and p-type adj layer	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:32	
28	BRS	13035	"light emitting device"	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:33	
29	BRS	671	"light emitting device" and semiconductor adj layers	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:34	
30	BRS	125	"light emitting device" and semiconductor adj layers and p-type adj layer	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:34	

	Type	Hits	Search Text	DBs	Time Stamp	Comments
31	BRS	87	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/14 13:31	
32	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and reflector adj layer	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:38	
33	BRS	2202163	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and reflector layer	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:39	
34	BRS	707	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and reflector layer and "ohmic layer"	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:39	
35	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and reflector adj layer and "ohmic layer"	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:40	
36	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and "ohmic layer"	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:41	

Type	Hits	Search Text	DBs	Time Stamp	Comments
37 BRS	2	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and reflect	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:43	
38 BRS	9	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and mirror	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:48	
39 BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and reproducer	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:48	
40 BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and reproduce	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:48	
41 BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and replicator	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:48	
42 BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and replicate	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:48	

	Type	Hits	Search Text	DBs	Time Stamp	Comments
43	BRS	0	"light emitting diode" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and replicate	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:49	
44	BRS	0	"light emitting diode" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and reproduce	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:49	
45	BRS	36	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/14 18:11	
46	BRS	13	"light emitting diode" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and mirror	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/12 10:50	
47	BRS	0	5351255.pn. and nickel and silver	USPAT	2001/03/13 10:49	
48	BRS	0	5351255.pn. and nickel	USPAT	2001/03/13 10:49	
49	BRS	1	5351255.pn.	USPAT	2001/03/13 11:54	
50	BRS	1	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and reflectivity	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/13 11:57	

	Type	Hits	Search Text	DBs	Time Stamp	Comments
51	BRS	12	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and contact adj resistance	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/13 11:59	
52	BRS	0	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and "ohmic layer" and "GaN"	USPAT	2001/03/14 13:31	
53	BRS	19	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and "GaN"	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/14 13:40	
54	BRS	1	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and reflectivity	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/14 13:41	
55	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and "light loss"	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/14 13:42	
56	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and absorbtion	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/14 13:47	

Type	Hits	Search Text	DBs	Time Stamp	Comments
57 BRS	4	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and absorb	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/14 13:42	
58 BRS	12	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and absorption	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/14 15:27	
59 BRS	21	"light emitting device" and "GaN" and reflectivity	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/14 15:29	
60 BRS	21	"light emitting device" and "GaN" and reflectivity	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/14 15:35	
61 BRS	3	"light emitting device" and "GaN" and "ohmic" and "multi layer" and reflectivity	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/14 17:07	
62 BRS	11	"light emitting device" and "GaN" and "ohmic" and reflectivity	USPAT; EPO; JPO; Derwent ; IBM TDB	2001/03/14 17:04	
63 BRS	1	5351255.PN.	USPAT	2001/03/14 18:11	

	Type	Hits	Search Text	DBs	Time Stamp	Comments
64	BRS	0	5351255.PN. AND 5585648.PN. AND 5932896.PN. AND 6190937.PN. AND 6057565.PN. AND 5990500.PN.	USPAT	2001/03/14 18:13	
65	BRS	6	5351255.PN. OR 5585648.PN. OR 5932896.PN. OR 6190937.PN. OR 6057565.PN. OR 5990500.PN.	USPAT	2001/03/14 18:13	

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	0	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and "ohmic layer" and "reflector layer"	USPAT; EPO; JPO; Derwent; IBM TDB	2001/03/15 09:36
2	BRS	4	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and ohmic and reflector	USPAT; EPO; JPO; Derwent; IBM TDB	2001/03/15 09:38
3	BRS	0	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and ohmic and reflector	EPO; JPO; Derwent; IBM TDB	2001/03/15 09:38
4	BRS	0	"light emitting device" and "p-type layer" and "n-type layer" and ohmic and reflector	EPO; JPO; Derwent; IBM TDB	2001/03/15 09:38
5	BRS	0	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and ohmic and mirror	EPO; JPO; Derwent; IBM TDB	2001/03/15 09:39
6	BRS	0	"light emitting device" and semiconductor adj material and "p-type " and "n-type " and ohmic and mirror	EPO; JPO; Derwent; IBM TDB	2001/03/15 09:39
7	BRS	0	"light emitting device" and semiconductor adj material and "p-type" and "n-type" and ohmic and mirror	EPO; JPO; Derwent; IBM TDB	2001/03/15 09:39

	Type	Hits	Search Text	DBs	Time Stamp
8	BRS	0	"light emitting device" and semiconductor adj material and "multi layers" and ohmic and mirror	EPO; JPO; Derwent; IBM TDB	2001/03/15 09:40
9	BRS	0	"light emitting device" and semiconductor and "multi layers" and ohmic and mirror	EPO; JPO; Derwent; IBM TDB	2001/03/15 09:40
10	BRS	0	"light emitting device" and semiconductor and "multi layers" and mirror	EPO; JPO; Derwent; IBM TDB	2001/03/15 09:41
11	BRS	0	"light emitting device" and "multi layers" and mirror and ohmic	EPO; JPO; Derwent; IBM TDB	2001/03/15 09:41
12	BRS	0	"light emitting device" and "multi layers" and ohmic	EPO; JPO; Derwent; IBM TDB	2001/03/15 09:41
13	BRS	8576	"light emitting device"	EPO; JPO; Derwent; IBM TDB	2001/03/15 09:41
14	BRS	6	"light emitting device" and ohmic adj layer	EPO; JPO; Derwent; IBM TDB	2001/03/15 09:42
15	BRS	0	"light emitting device" and ohmic adj layer and reflector	EPO; JPO; Derwent; IBM TDB	2001/03/15 09:42

	Type	Hits	Search Text	DBs	Time Stamp
16	BRS	0	"light emitting device" and ohmic adj layer and mirror	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:42
17	BRS	1	"light emitting device" and ohmic and mirror	EPO; JPO; Derwen t; IBM TDB	2001/03/15 09:42